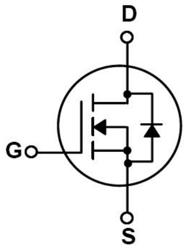
TO-252 N MOS N-CHANNEL MOSFET in a TO-252 Plastic Package.

DS dv/dt

Low $R_{DS(ON)}$, Low gate charge, Low Crss , Fast switching, Improved dv/dt capability.

DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.



PIN1 G PIN 2 D PIN 3 S PIN 4 D

See Marking Instructions.

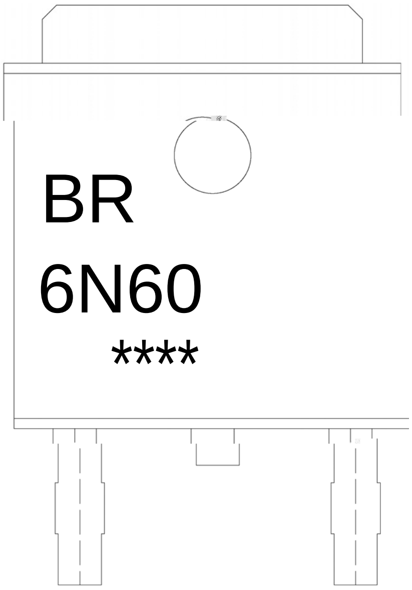
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	I_D(Tc=25)	5.5	A
Drain Current	I_D(Tc=100)	3.3	A
Drain Current - Pulsed	I_{DM}	22	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	300	mJ
Repetitive Avalanche Energy	E_{AR}	12.5	mJ
Avalanche Current	I_{AR}	5.5	A
Power Dissipation	P_D(Tc=25)	40	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250µA	600			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V V_{GS}=0V			1	µA
		V_{DS}=480V T_C				

	0.90
	0.10

D1	5.10	5.50	K	0.00

TO-252



BR

6N60

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Note:

BR:	Company Code
6N60:	Product Type.
****:	Lot No. Code, code change with Lot No.

Rev.D Nov.-2015